SGS-THOMSON
MICROELECTRONICS

STANDARD CELLS

CB 22000 SERIES

0.7 micron, double level metal HCMOS Tecnology. Typical delay 0.3ns for 2-input NAND gate

Process Technology	Density (gates/mm^2)	Delay (ns)	Gate Power (µw/Gate/MHz)	Single Output Drive (mA)	I/O Interface	Compilers
0.7 µm, double level metal	800	0.3 typ. for 2-Input NAND gate ND2P	5	up to 24	TTL, CMOS, EISA, ISA, MCA, SCSI	SPRAM 80K bits max DPRAM 64K bit max ROM 64K bits max FIFO 32K bits max MULTIPLIER 6x6 to 64x64 bit

CB 35000 SERIES

0.5 micron, triple level metal HCMOS Tecnology. Typical delay .210ns for 2-input NAND gate (3.3 V)

Process Technology	Density (gates/mm^2)	Delay (ns)	Gate Power (µw/Gate/MHz)	Single Output Drive (mA)	I/O Interface	Compilers
0.5 µm, triple level metal	5500	.210	.7	up to 24	LVCMOS LVTTL GTL PECL IEEE LVDS	SPRAM 256K bit max DPRAM 64K bit max ROM 512K bits max MULTIPLIER 64x64 bits max

STANDARD PACKAGE RANGE

Package	Pins
PQFP	64 to 208
TQFP	100 to 176